

TLV6003 980nA 16V 精密轨至轨输入和输出运算放大器

1 特性

- 低功耗运行：1.2 μ A（最大值）
- 低输入失调电压：550 μ V（最大值）
- 高达 18V 的反向电池保护
- 轨至轨输入/输出
- 增益带宽积：5.5kHz
- 额定温度范围：
 $T_A = -40^{\circ}\text{C}$ 至 $+125^{\circ}\text{C}$
- 工作温度范围：
 $T_A = -55^{\circ}\text{C}$ 至 $+125^{\circ}\text{C}$
- 输入共模范围超过电源轨：
 -0.1V 至 $V_{CC} + 5\text{V}$
- 电源电压范围：2.5V 至 16V
- 小封装：
 - 5 引脚 SOT-23

2 应用

- 流量变送器
- 压力变送器
- 运动检测器（PIR、uWave 等）
- 血糖监测仪
- 气体检测仪

3 说明

TLV6003 是一款纳瓦级功耗运算放大器，每个通道仅消耗 980nA 的电流，同时提供极低的最大失调电压。逆向电池保护可在电池安装不当产生过大电流时保护放大器。在恶劣环境下，输入电压可以比正电源轨高 5V，不会损坏器件。

低电源电流与低输入偏置电流耦合，使该器件可与高串联电阻输入源（如 PIR 运动检测仪和一氧化碳传感器）一起使用。在 550 μ V (25 $^{\circ}\text{C}$) 的低最大失调电压、120dB 的典型 CMRR 和 112dB 的最小开环增益 (2.7V) 情况下可以保持直流精度。

最高额定工作电源电压为 2.5V 至 16V，电气特性在 2.7V、5V 和 15V 下指定。2.5V 工作电压使该器件与锂离子电池供电系统兼容，从而使 TLV6003 成为输入信号增益和低功耗微控制器（如 TI 的 MSP430）缓冲的理想之选。

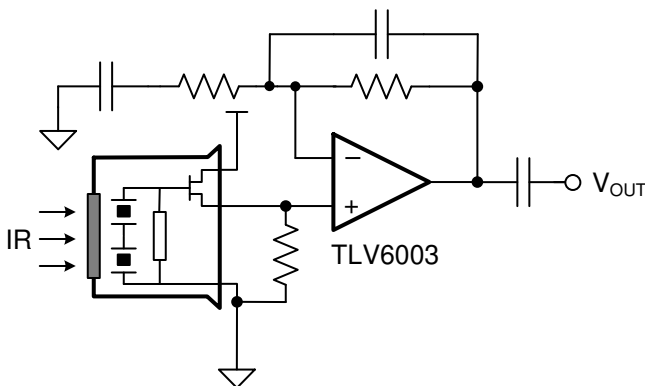
TLV6003 采用小型 SOT-23 封装。

器件信息⁽¹⁾

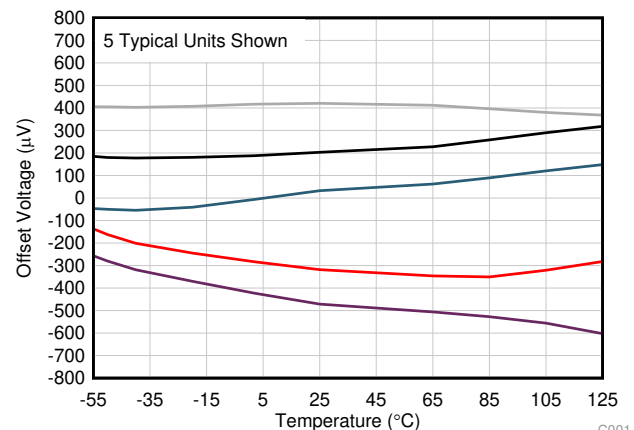
器件型号	封装	封装尺寸（标称值）
TLV6003	SOT-23 (5)	2.90mm x 1.60mm

(1) 如需了解所有可用封装，请参阅数据表末尾的封装选项附录。

PIR 运动检测器缓冲器



失调电压与温度间的关系



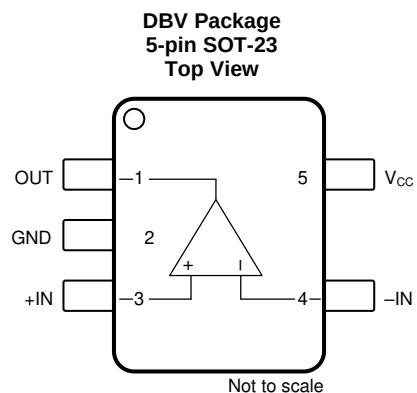
目录

1	特性	1	8	Application and Implementation	14
2	应用	1	8.1	Application Information.....	14
3	说明	1	8.2	Typical Application	15
4	修订历史记录	2	9	Power Supply Recommendations	18
5	Pin Configuration and Functions	3	10	Layout	18
6	Specifications	4	10.1	Layout Guidelines	18
6.1	Absolute Maximum Ratings	4	10.2	Layout Example	18
6.2	ESD Ratings.....	4	11	器件和文档支持	19
6.3	Recommended Operating Conditions.....	4	11.1	器件支持	19
6.4	Thermal Information – TLV6003	4	11.2	文档支持	19
6.5	Electrical Characteristics.....	5	11.3	接收文档更新通知	19
6.6	Typical Characteristics	7	11.4	社区资源	19
7	Detailed Description	12	11.5	商标	19
7.1	Overview	12	11.6	静电放电警告	19
7.2	Functional Block Diagram	12	11.7	Glossary	19
7.3	Feature Description.....	13	12	机械、封装和可订购信息	19
7.4	Device Functional Modes.....	13			

4 修订历史记录

日期	修订版本	说明
2019 年 10 月	*	初始发行版。

5 Pin Configuration and Functions



Pin Functions

PIN		I/O	DESCRIPTION
NAME	DBV		
OUT	1	O	Output
GND	2	–	Negative (lowest) power supply
+IN	3	I	Noninverting input
–IN	4	I	Inverting input
VCC	5	–	Positive (highest) power supply

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

			MIN	MAX	UNIT
V _{CC}	Supply voltage ⁽²⁾		–18	17	V
V _{IN+} , V _{IN–}	Input voltage	Singe-ended and common-mode input voltage, V _{ICR}	–0.3	V _{CC} + 5	V
		Differential, V _{ID}		±20	
	Input current (any input)			±10	mA
I _O	Output current			±10	mA
	Continuous total power dissipation		See Dissipation Rating		
T _J	Maximum junction temperature		–55	150	°C
T _{stg}	Storage temperature		–65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltage values, except differential voltages, are with respect to GND

6.2 ESD Ratings

			VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±450	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1000	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

			MIN	NOM	MAX	UNIT
V _{CC}	Supply Voltage	Single Supply	2.5		16	V
		Split Supply	±1.25		±8	
T _A	Operating free-air temperature		–55		125	°C

6.4 Thermal Information – TLV6003

THERMAL METRIC ⁽¹⁾		TLV6003	UNIT
		DBV	
		5 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	166.0	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	89.9	°C/W
R _{θJB}	Junction-to-board thermal resistance	36.5	°C/W
ψ _{JT}	Junction-to-top characterization parameter	14.0	°C/W
ψ _{JB}	Junction-to-board characterization parameter	36.3	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

6.5 Electrical Characteristics

at $T_A = 25^\circ\text{C}$, $V_{CC} = 2.7\text{ V}$, 5 V , and 15 V , $V_{ICR} = V_O = V_{CC}/2$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
DC PERFORMANCE							
V _{IO}	Input offset voltage ⁽¹⁾				390	±550	μV
		T _A = −55°C to +125°C				1500	
dV _{IO} /dT	Offset voltage drift	T _A = −55°C to +125°C			2		μV/°C
CMRR	Common-mode rejection ratio	V _{ICR} = 0 V to V _{CC}	V _{CC} = 2.7 V	63	120		dB
			V _{CC} = 2.7 V, T _A = −40°C to +125°C	60			
			V _{CC} = 5 V	66	120		
			V _{CC} = 5 V, T _A = −40°C to +125°C	63			
			V _{CC} = 15 V	76	120		
			V _{CC} = 15 V, T _A = −40°C to +125°C	75			
A _{OL}	Open-loop gain	V _{CC} = 2.7 V, 0.2 V < V _O < V _{CC} − 0.2 V, R _L = 500 kΩ			112		dB
		V _{CC} = 15 V, 0.2 V < V _O < V _{CC} − 0.2 V, R _L = 500 kΩ			123		dB
INPUT							
I _{IO}	Input offset current				25	250	pA
		T _A = −40°C to +125°C				1200	
I _{IB}	Input bias current				100	250	pA
		T _A = −40°C to +125°C				2000	
r _{i(d)}	Differential input resistance				300		MΩ
C _{i(c)}	Common-mode input capacitance	f = 100 kHz			3		pF
DYNAMIC PERFORMANCE							
UGBW	Unity gain bandwidth	R _L = 500 kΩ, C _L = 100 pF			5.5		kHz
SR	Slew rate at unity gain	V _{O(pp)} = 0.8 V, R _L = 500 kΩ, C _L = 100 pF			2.5		V/ms
PM	Phase margin	R _L = 500 kΩ, C _L = 100 pF			60		°
	Gain margin	R _L = 500 kΩ, C _L = 100 pF			15		dB
t _s	Settling time	V _{CC} = 2.7 or 5 V, V _{(STEP)PP} = 1 V, A _V = −1, C _L = 100 pF, R _L = 100 kΩ	0.1%		1.84		ms
		V _{CC} = 15 V, V _{(STEP)PP} = 1 V, A _V = −1, C _L = 100 pF, R _L = 100 kΩ	0.1%		6.1		
			0.01%		32		
NOISE PERFORMANCE							
V _n	Equivalent input noise voltage	f = 10 Hz			800		nV/√Hz
		f = 100 Hz			500		
I _n	Equivalent input noise current	f = 100 Hz			8		fA/√Hz
OUTPUT							
V _{OL}	Voltage output swing from the positive rail	I _{OL} = 2 μA (sourcing)		V _{CC} − 0.05	V _{CC} − 0.02		V
			T _A = −40°C to +125°C	V _{CC} − 0.07			
		I _{OL} = 50 μA (sourcing)		V _{CC} − 0.08	V _{CC} − 0.05		
			T _A = −40°C to +125°C	V _{CC} − 0.1			
V _{OH}	Voltage output swing from the negative rail	I _{OH} = 2 μA (sinking)			0.090	0.150	
			T _A = −40°C to +125°C			0.180	
		I _{OH} = 50 μA (sinking)			0.180	0.230	
			T _A = −40°C to +125°C			0.260	
I _O	Output current	V _O = 0.5 V from rail			±200		μA

(1) Input offset voltage and offset voltage drift are specified by characterization from $T_A = -55^\circ\text{C}$ to $+125^\circ\text{C}$. All other temperature specifications cover the range of $T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$, as listed in the test conditions column.

Electrical Characteristics (continued)

at $T_A = 25^\circ\text{C}$, $V_{CC} = 2.7\text{ V}$, 5 V , and 15 V , $V_{ICR} = V_O = V_{CC}/2$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
POWER SUPPLY							
I _{CC}	Supply current	V _{CC} = 2.7 V and 5 V		980		1200	nA
			T _A = −40°C to +125°C	1350			
		V _{CC} = 15 V		1000		1250	
			T _A = −40°C to +125°C	1400			
	Reverse supply current	V _{CC} = −18 V, V _{IN} = 0 V, V _O = open current		50			nA
PSRR	Power supply rejection ratio (ΔV _{CC} /ΔV _{OS})	V _{CC} = 2.7 to 5 V, no load		90	100		dB
			T _A = −40°C to 125°C	85			
		V _{CC} = 5 to 15 V, no load		100	110		
			T _A = −40°C to 125°C	95			

6.6 Typical Characteristics

at $T_A = 25^\circ\text{C}$ and $V_{CC} = 5\text{ V}$ (unless otherwise noted)

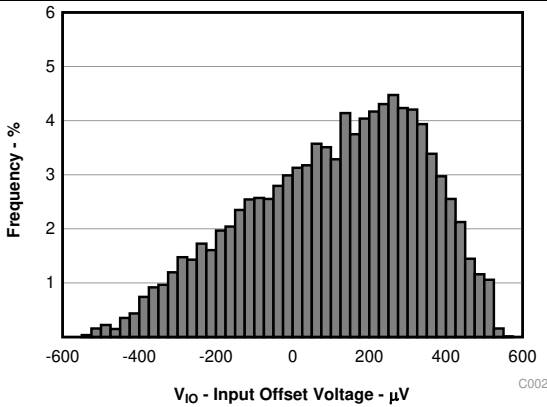


图 1. Input Offset Voltage Histogram

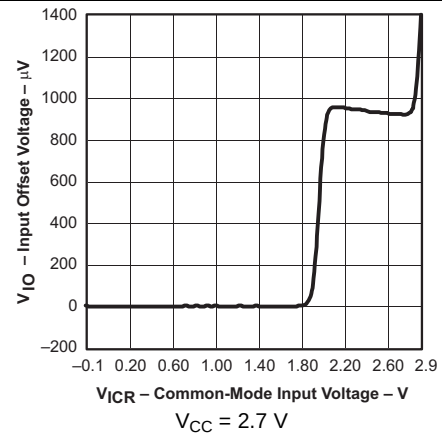


图 2. Input Offset Voltage vs Common-Mode Input Voltage

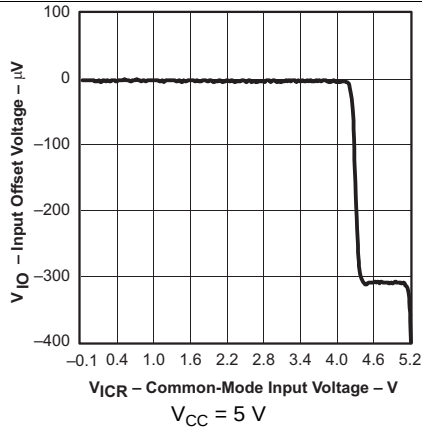


图 3. Input Offset Voltage vs Common-Mode Input Voltage

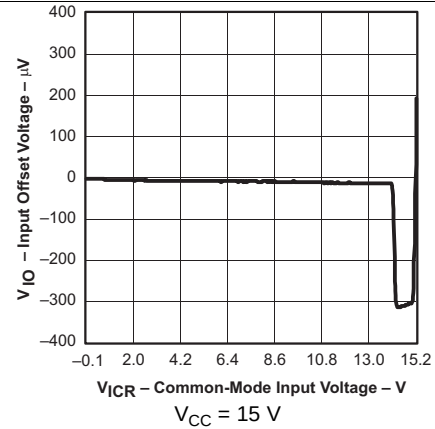


图 4. Input Offset Voltage vs Common-Mode Input Voltage

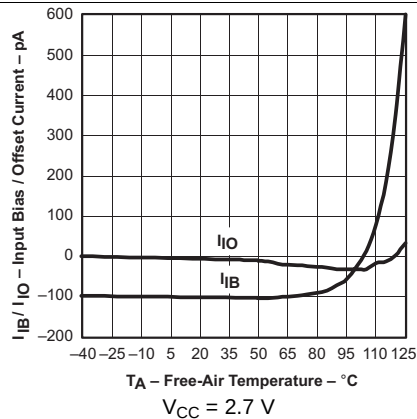


图 5. Input Bias Current and Offset Current vs Free-Air Temperature

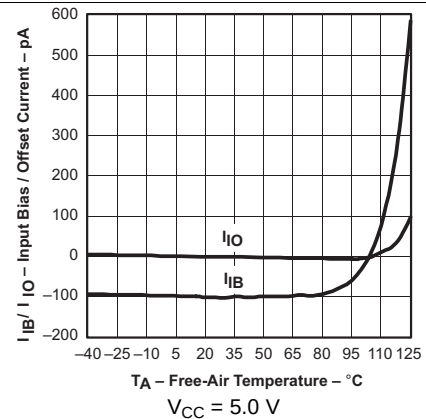


图 6. Input Bias Current and Offset Current vs Common-Mode Input Voltage

Typical Characteristics (接下页)

at $T_A = 25^\circ\text{C}$ and $V_{CC} = 5\text{ V}$ (unless otherwise noted)

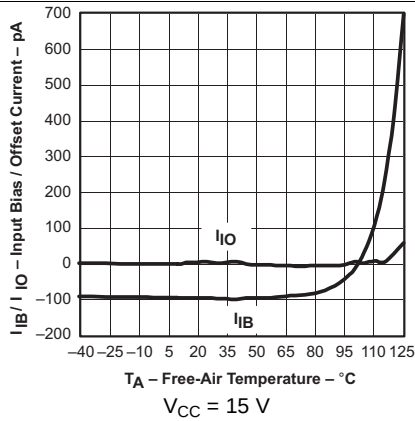


图 7. Input Bias Current and Offset Current vs Free-Air Temperature

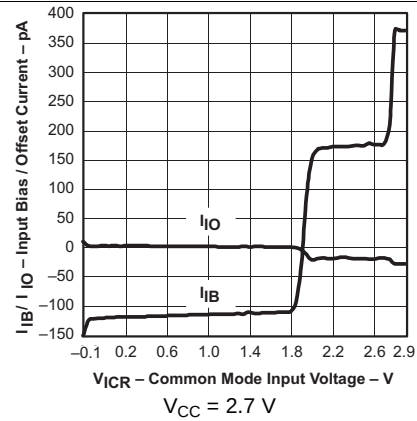


图 8. Input Bias Current and Offset Current vs Common-Mode Input Voltage

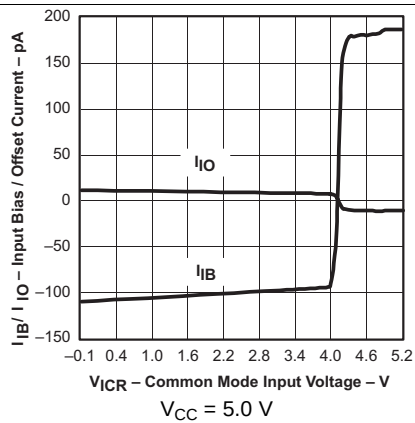


图 9. Input Bias Current and Offset Current vs Common-Mode Input Voltage

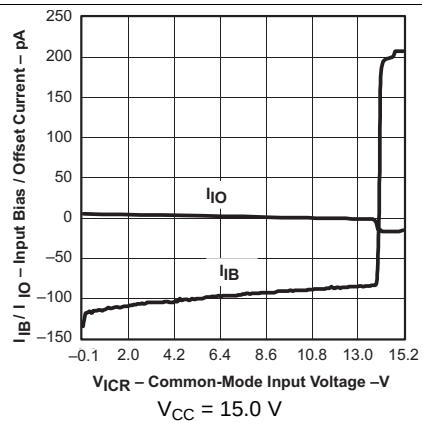


图 10. Input Bias Current and Offset Current vs Common-Mode Input Voltage

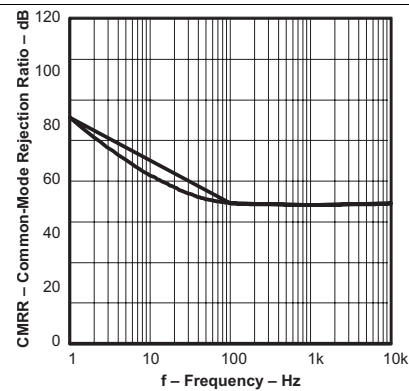


图 11. Common-Mode Rejection Ratio vs Frequency

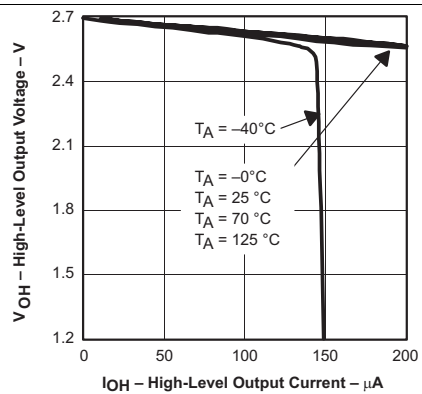


图 12. High-Level Output Voltage vs High-Level Output Current

Typical Characteristics (接下页)

at $T_A = 25^\circ\text{C}$ and $V_{CC} = 5\text{ V}$ (unless otherwise noted)

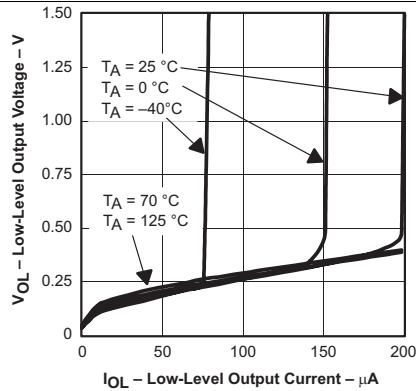


图 13. Low-Level Output Voltage vs Low-Level Output Current

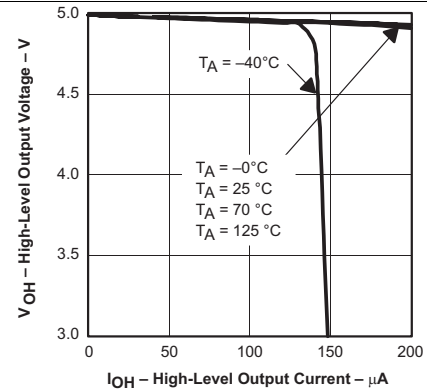


图 14. High-Level Output Voltage vs High-Level Output Current

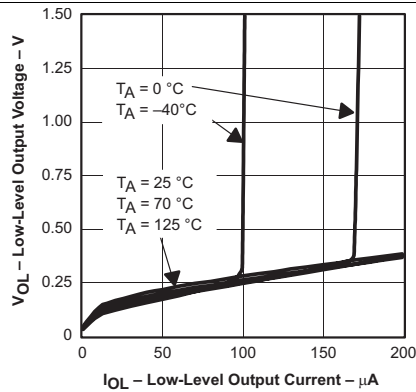


图 15. Low-Level Output Voltage vs Low-Level Output Current

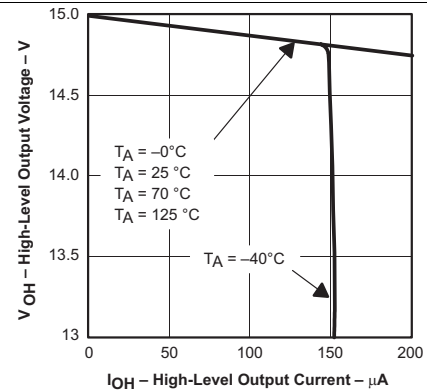


图 16. High-Level Output Voltage vs High-Level Output Current

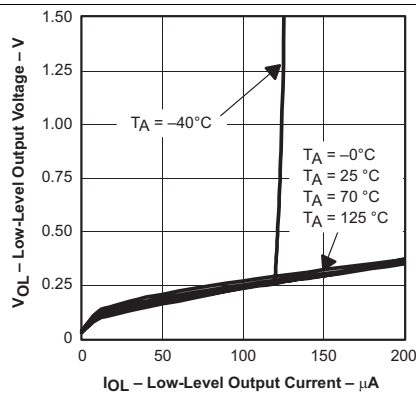


图 17. Low-Level Output Voltage vs Low-Level Output Current

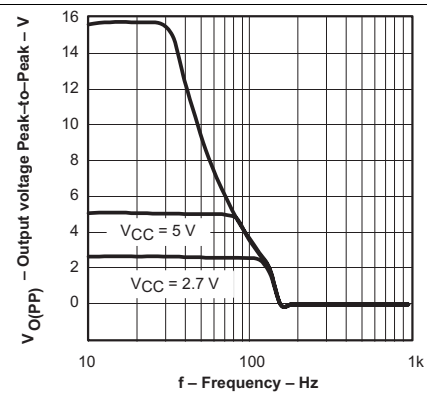


图 18. Output Voltage Peak-to-Peak vs Frequency

Typical Characteristics (接下页)

at $T_A = 25^\circ\text{C}$ and $V_{CC} = 5\text{ V}$ (unless otherwise noted)

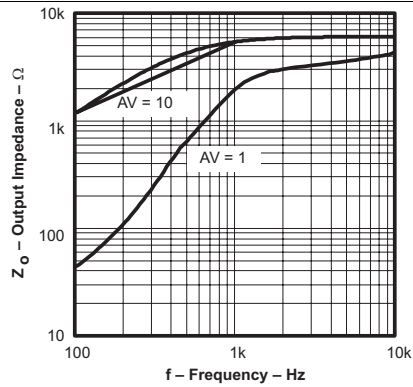


图 19. Output Impedance vs Frequency

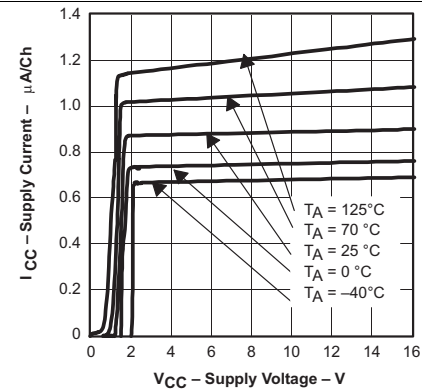


图 20. Supply Current vs Supply Voltage

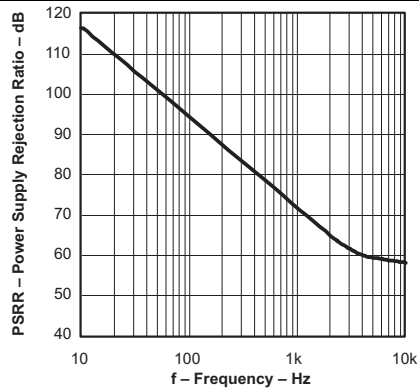


图 21. Power Supply Rejection Ratio vs Frequency

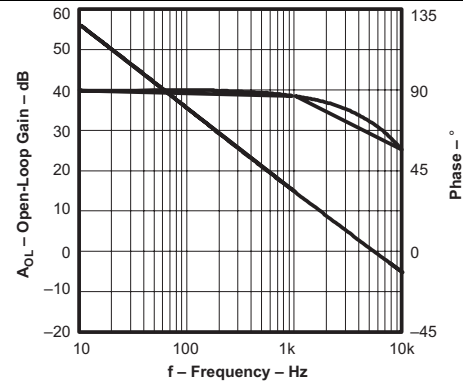


图 22. Open-Loop Gain and Phase vs Frequency

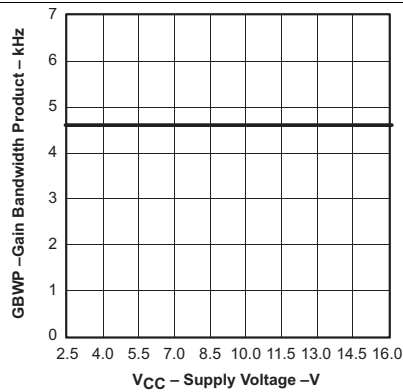


图 23. Gain Bandwidth Product vs Supply Voltage

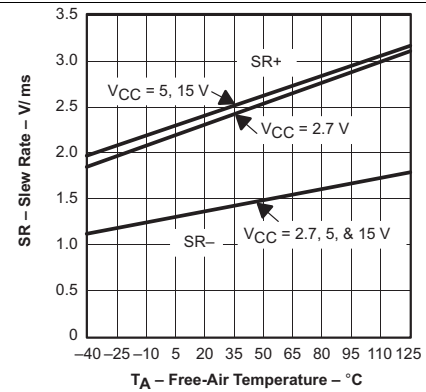


图 24. Slew Rate vs Free-Air Temperature

Typical Characteristics (接下页)

at $T_A = 25^\circ\text{C}$ and $V_{CC} = 5\text{ V}$ (unless otherwise noted)

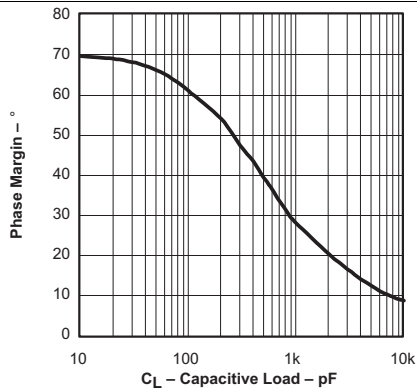


图 25. Phase Margin vs Capacitive Load

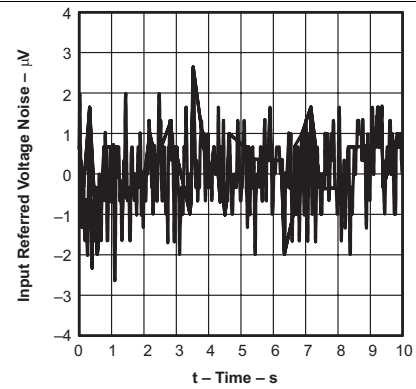


图 26. Voltage Noise Over a 10-Second Period

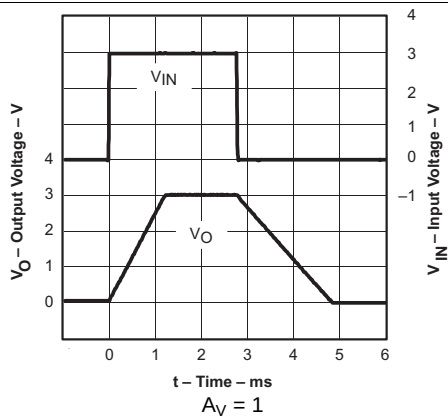


图 27. Large-Signal Step Response

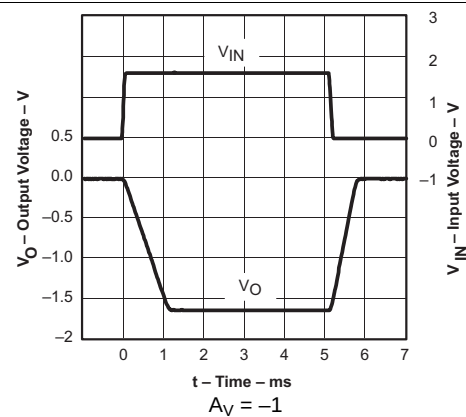


图 28. Large-Signal Step Response

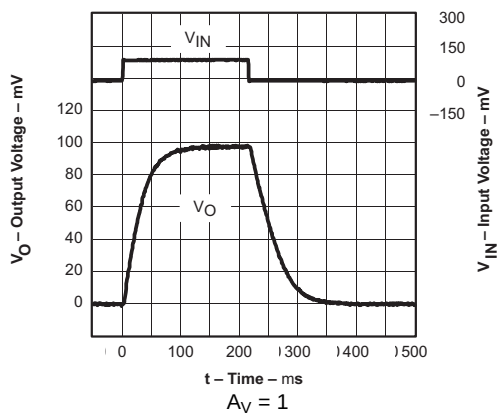


图 29. Small-Signal Step Response

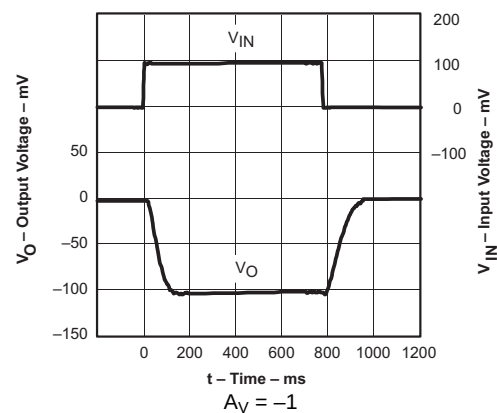


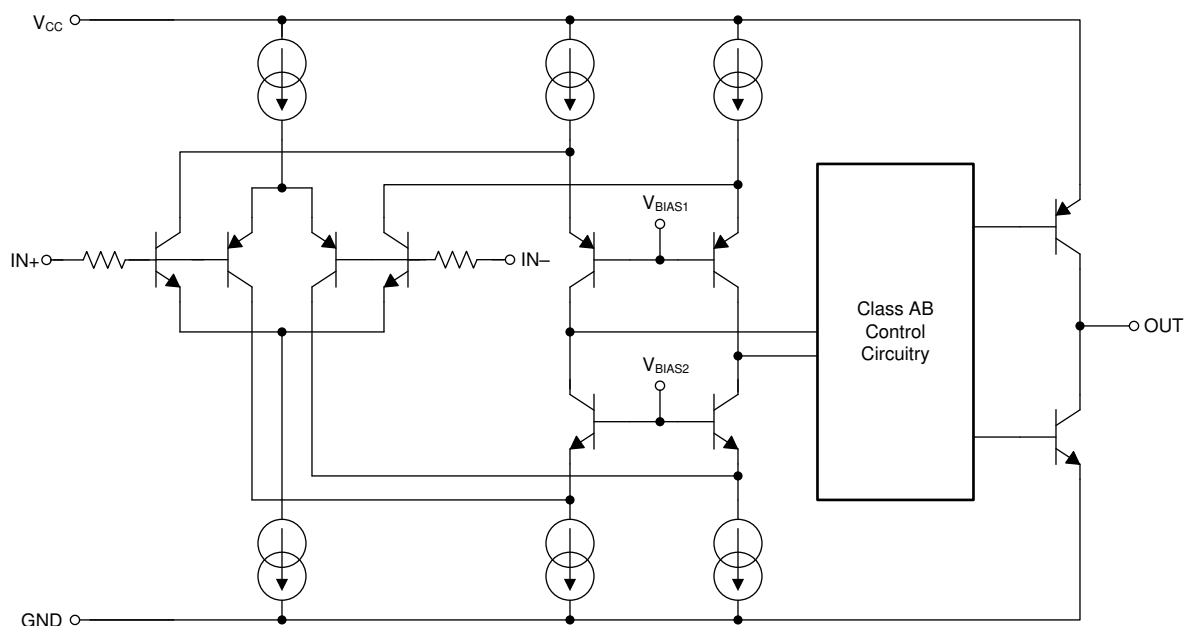
图 30. Small-Signal Step Response

7 Detailed Description

7.1 Overview

The TLV6003 is a nanopower operational amplifier consuming only 980 nA per channel, while offering very low maximum offset. Reverse battery protection guards the amplifier from overcurrent conditions due to improper battery installation. The TLV6003 is based on a rail-to-rail bipolar technology that is specifically designed to allow high common-mode-range functionality. For harsh environments, the inputs can be taken 5 V greater than the positive supply rail without damage to the device. Offset is specified by characterization to an ambient temperature of -55°C , making the TLV6003 a good choice for low-temperature industrial automation.

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 Reverse-Battery Protection

The TLV6003 is protected against reverse-battery voltage up to 18 V. When subjected to reverse-battery conditions, the supply current is typically 50 nA at 25°C (inputs grounded and outputs open). This current is determined by the leakage of internal Schottky diodes, and therefore increases as the ambient temperature increases.

When subjected to reverse-battery conditions, and negative voltages are applied to the inputs or outputs, the input ESD structure conducts current; limit this current to less than 10 mA. If the inputs or outputs are referred to ground rather than midrail, no extra precautions are required.

7.3.2 Common-Mode Input Range

The TLV6003 has rail-to-rail inputs and outputs. For common-mode inputs from -0.1 V to $V_{CC} - 0.8\text{ V}$, a PNP differential pair provides the gain.

For inputs between $V_{CC} - 0.8\text{ V}$ and V_{CC} , two NPN emitter followers buffering a second PNP differential pair provide the gain.

This special combination of a NPN and PNP differential pair enables the inputs to be taken 5 V greater than V_{CC} . As the inputs rise to greater than V_{CC} , the NPNs change from functioning as transistors to functioning as diodes. This change leads to an increase in input bias current. The second PNP differential pair continues to function normally as the inputs exceed V_{CC} .

The TLV6003 has a negative common-mode input voltage range that can fall to less than V_{GND} by 100 mV. If the inputs are taken to less than $V_{GND} - 0.1$, reduced open-loop gain will be observed.

7.4 Device Functional Modes

The TLV6003 has a single functional mode and is operational when the power-supply voltage is greater than 2.5 V. The maximum specified power-supply voltage for the TLV6003 is 16 V.

8 Application and Implementation

注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

8.1.1 Drive a Capacitive Load

The TLV6003 is internally compensated for stable unity-gain operation, with a 5.5-kHz typical gain bandwidth. However, the unity gain follower is the most sensitive configuration to capacitive load. The combination of a capacitive load placed directly on the output of an amplifier along with the amplifier output impedance creates a phase lag, which reduces the phase margin of the amplifier. If the phase margin is significantly reduced, the response will be underdamped, which causes peaking in the transfer function. This condition creates very low phase margin, and leads to excessive ringing or oscillations.

In order to drive heavy (> 50 pF) capacitive loads, an isolation resistor (R_{ISO}) must be used, as shown in 图 31. By using this isolation resistor, the capacitive load is isolated from the amplifier output. The higher the value of R_{ISO} , the more stable the amplifier. If the value of R_{ISO} is sufficiently high, the feedback loop is stable, independent of the value of C_L . However, larger values of R_{ISO} result in reduced output swing and reduced output current drive. The recommended value for R_{ISO} is 30 k Ω to 50 k Ω .

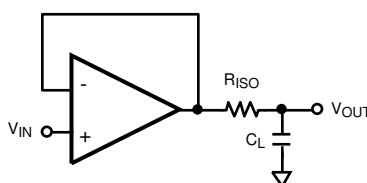


图 31. Resistive Isolation of Capacitive Load

8.2 Typical Application

图 32 shows a simple micropower potentiostat circuit for use with three-terminal unbiased CO sensors; although, the design is applicable to many other type of three-terminal gas sensors or electrochemical cells.

The basic sensor has three electrodes: the sense or working electrode (WE), counter electrode (CE) and reference electrode (RE). A current flows between the CE and WE proportional to the detected concentration.

The RE monitors the potential of the internal reference point. For an unbiased sensor, the WE and RE electrodes must be maintained at the same potential by adjusting the bias on CE. Through the potentiostat circuit formed by U1, the servo feedback action maintains the RE pin at a potential set by V_{REF} .

R1 maintains stability due to the large capacitance of the sensor.

C1 and R2 form the potentiostat integrator and set the feedback time constant.

U2 forms a transimpedance amplifier (TIA) to convert the resulting sensor current into a proportional voltage. The transimpedance gain, and resulting sensitivity, is set by R_F according to 公式 1.

$$V_{TIA} = (-I * R_F) + V_{REF} \quad (1)$$

R_L is a load resistor with a value that is normally specified by the sensor manufacturer (typically, 10 Ω). The potential at WE is set by the applied V_{REF} .

Riso provides capacitive isolation and, combined with C2, form the output filter and ADC reservoir capacitor to drive the ADC.

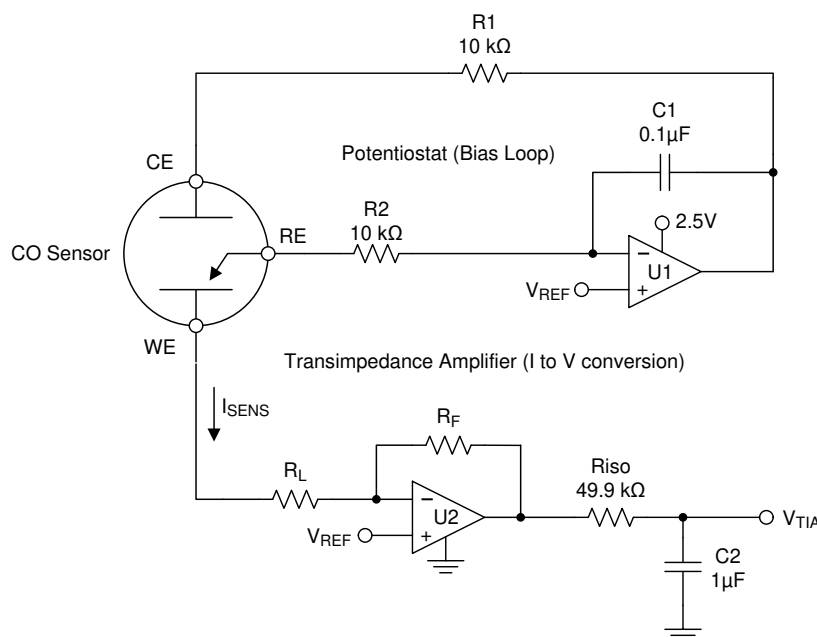


图 32. Three Terminal CO Gas Sensor

Typical Application (接下页)

8.2.1 Design Requirements

For this example, an electrical model of a CO sensor is used to simulate the sensor performance, as shown in 图 33. The simulation is designed to model a CO sensor with a sensitivity of 69 nA/ppm. The supply voltage and maximum ADC input voltage is 2.5 V, and the maximum concentration is 300 ppm.

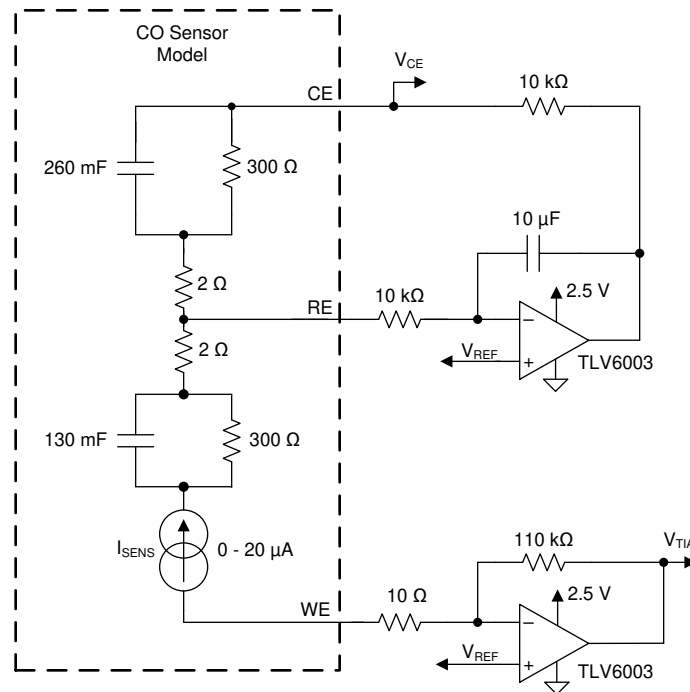


图 33. CO Sensor Simulation Schematic

表 1. Design Parameters

DESIGN PARAMETER	EXAMPLE VALUE
Supply voltage	2.5 V
Amplifier quiescent current	< 2 μ A
Transimpedance amplifier sensitivity	110 mV/ μ A

8.2.2 Detailed Design Procedure

First, determine the V_{REF} voltage. This voltage is a compromise between maximum headroom and resolution, as well as allowance for the minimum swing on the CE terminal because the CE terminal generally goes negative in relation to the RE potential as the concentration (sensor current) increases. Bench measurements found the difference between CE and RE to be 180 mV at 300 ppm for this particular sensor.

To allow for negative CE swing, *footroom*, and voltage drop across the 10-k Ω resistor, 300 mV is chosen for V_{REF} .

Therefore, 300 mV is used as the minimum V_{ZERO} to add some headroom.

$$V_{ZERO} = V_{REF} = 300 \text{ mV}$$

where

- V_{ZERO} is the zero concentration voltage.
- V_{REF} is the reference voltage (300 mV).

Next, calculate the maximum sensor current at highest expected concentration:

$$I_{SENSMAX} = I_{PERPPM} * \text{ppmMAX} = 69 \text{ nA} * 300 \text{ ppm} = 20.7 \text{ }\mu\text{A}$$

where

- $I_{SENSMAX}$ is the maximum expected sensor current.
- I_{PERPPM} is the manufacturer specified sensor current in Amps per ppm.
- ppmMAX is the maximum required ppm reading.

Then, find the available output swing range greater than the reference voltage available for the measurement:

$$V_{SWING} = V_{OUTMAX} - V_{ZERO} = 2.5 \text{ V} - 0.3 \text{ V} = 2.2 \text{ V}$$

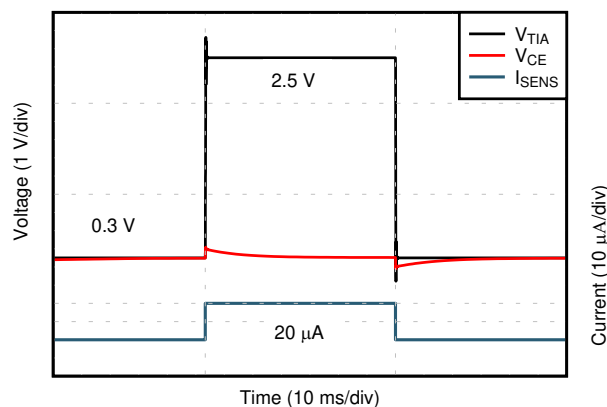
where

- V_{SWING} is the expected change in output voltage
- V_{OUTMAX} is the maximum amplifier output swing (usually near V_{CC})

Finally, calculate the transimpedance resistor (R_F) value using the maximum swing and the maximum sensor current:

$$R_F = V_{SWING} / I_{SENSMAX} = 2.2 \text{ V} / 20.7 \text{ }\mu\text{A} = 106.28 \text{ k}\Omega \text{ (use } 110 \text{ k}\Omega \text{ for a common value)}$$

8.2.3 Application Curve



C012

图 34. Sensor Transient Response to Simulated 300-ppm CO Exposure

9 Power Supply Recommendations

The TLV6003 is specified for operation from 2.5 V to 16 V (± 1.25 V to ± 8 V) over a -40°C to $+125^{\circ}\text{C}$ temperature range.

CAUTION

Supply voltages larger than 17 V can permanently damage the device.

For proper operation, the power supplies must be properly decoupled. For decoupling the supply lines, place 100 nF capacitors as close as possible to the operational amplifier power supply pins. For single-supply operation, place a capacitor between V_{CC} and GND supply leads. For dual supplies, place one capacitor between V_{CC} and ground, and one capacitor between GND and ground.

Low-bandwidth nanopower devices do not have good high-frequency (> 1 kHz) AC PSRR rejection against high-frequency switching supplies and other 1-kHz and greater noise sources. Therefore, use extra supply filtering if kilohertz or greater noise is expected on the power supply lines.

10 Layout

10.1 Layout Guidelines

- Bypass the V_{CC} pin to ground with a low ESR capacitor.
- The best placement is closest to the V_{CC} and ground pins.
- Take care to minimize the loop area formed by the bypass capacitor connection between V_{CC} and ground.
- Connect the ground pin to the PCB ground plane at the pin of the device.
- Place the feedback components as close as possible to the device to minimize strays.

10.2 Layout Example

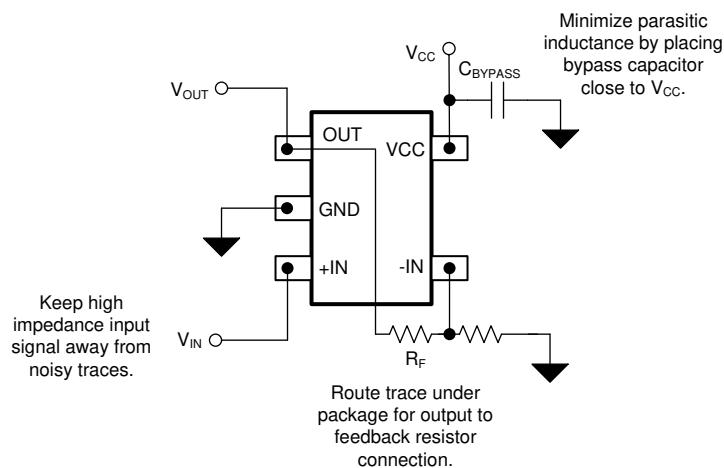


图 35. SOT-23 Layout Example (Top View)

11 器件和文档支持

11.1 器件支持

11.1.1 开发支持

- [《基于 SPICE 的 TINA-TI 模拟仿真程序》](#)
- [DIP 适配器评估模块](#)
- [TI 通用运算放大器评估模块](#)
- [TI 滤波器设计工具](#)

11.2 文档支持

11.2.1 相关文档

请参阅如下相关文档：

- [《单电源、低侧、单向电流检测电路》应用报告](#)
- [《使用纳瓦级功耗运算放大器简化功率敏感型工厂和楼宇自动化系统中的环境测量》应用手册](#)
- [《由锂离子电池供电的个人电子产品中的 GPIO 引脚电源信号链》应用简介](#)

11.3 接收文档更新通知

要接收文档更新通知，请导航至 [ti.com](#) 上的器件产品文件夹。单击右上角的[通知我进行注册](#)，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

11.4 社区资源

[TI E2E™ support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

11.5 商标

E2E is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

11.6 静电放电警告



ESD 可能会损坏该集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理措施和安装程序，可能会损坏集成电路。

ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

11.7 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

12 机械、封装和可订购信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。数据如有变更，恕不另行通知，且不会对此文档进行修订。如需获取此数据表的浏览器版本，请查阅左侧的导航栏。

重要声明和免责声明

TI 均以“原样”提供技术性 & 可靠性数据（包括数据表）、设计资源（包括参考设计）、应用或其他设计建议、网络工具、安全信息和其他资源，不保证其中不含任何瑕疵，且不做任何明示或暗示的担保，包括但不限于对适销性、适合某特定用途或不侵犯任何第三方知识产权的暗示担保。

所述资源可供专业开发人员应用 TI 产品进行设计使用。您将对以下行为独自承担全部责任：(1) 针对您的应用选择合适的 TI 产品；(2) 设计、验证并测试您的应用；(3) 确保您的应用满足相应标准以及任何其他安全、安保或其他要求。所述资源如有变更，恕不另行通知。TI 对您使用所述资源的授权仅限于开发资源所涉及 TI 产品的相关应用。除此之外不得复制或展示所述资源，也不提供其它 TI 或任何第三方的知识产权授权许可。如因使用所述资源而产生任何索赔、赔偿、成本、损失及债务等，TI 对此概不负责，并且您须赔偿由此对 TI 及其代表造成的损害。

TI 所提供产品均受 TI 的销售条款 (<http://www.ti.com.cn/zh-cn/legal/termsofsale.html>) 以及 [ti.com.cn](http://www.ti.com.cn) 上或随附 TI 产品提供的其他可适用条款的约束。TI 提供所述资源并不扩展或以其他方式更改 TI 针对 TI 产品所发布的可适用的担保范围或担保免责声明。

邮寄地址：上海市浦东新区世纪大道 1568 号中建大厦 32 楼，邮政编码：200122
Copyright © 2019 德州仪器半导体技术（上海）有限公司

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TLV6003DBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	1NE9	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSELETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

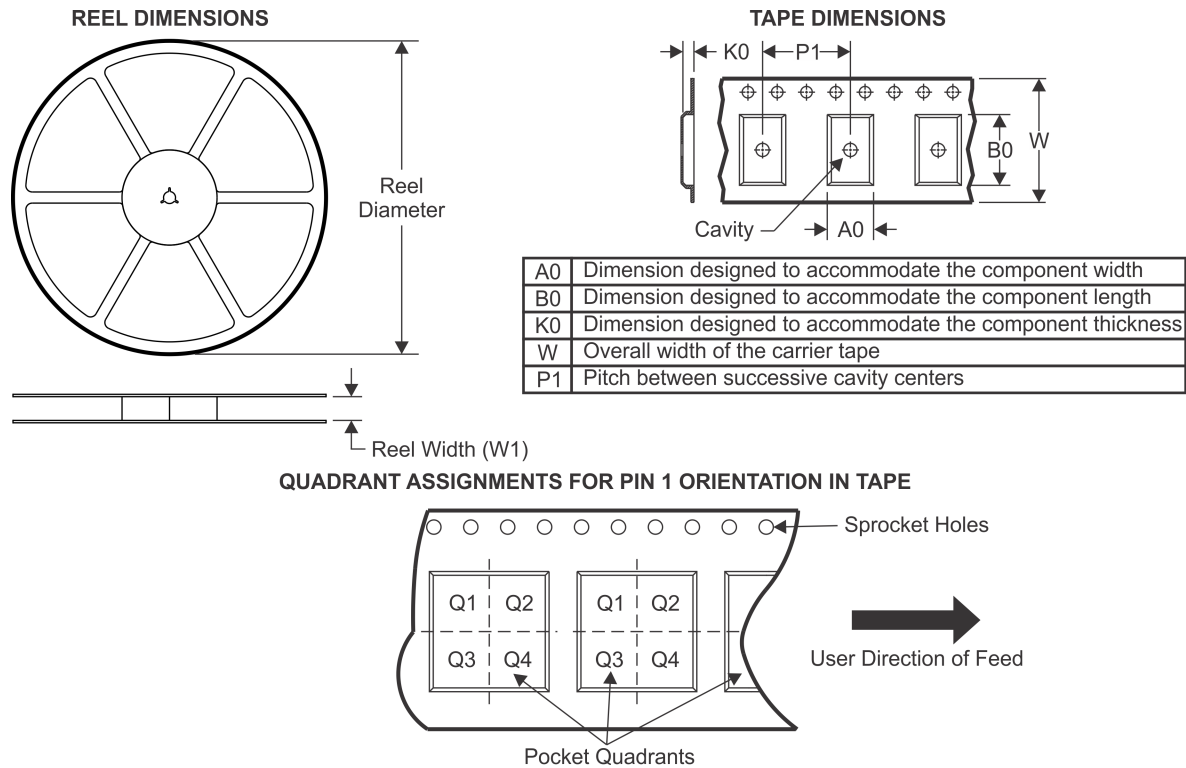
(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

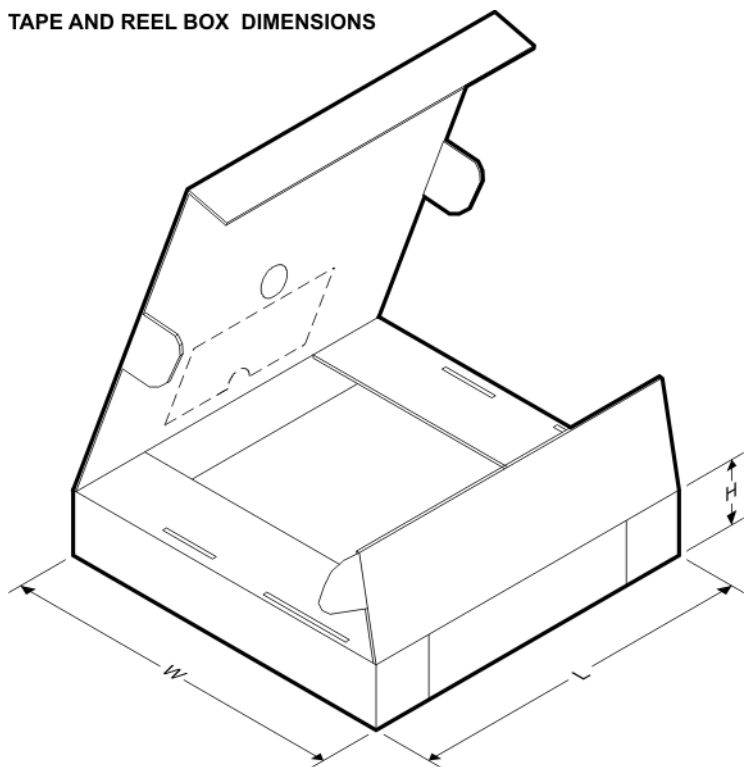
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV6003DBVR	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

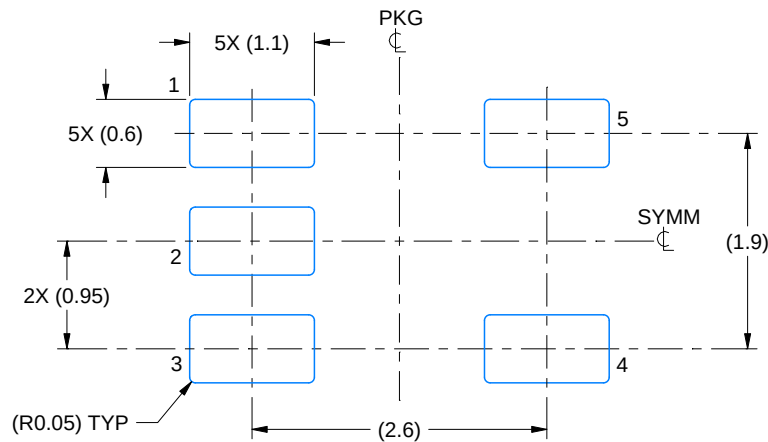
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLV6003DBVR	SOT-23	DBV	5	3000	210.0	185.0	35.0

EXAMPLE BOARD LAYOUT

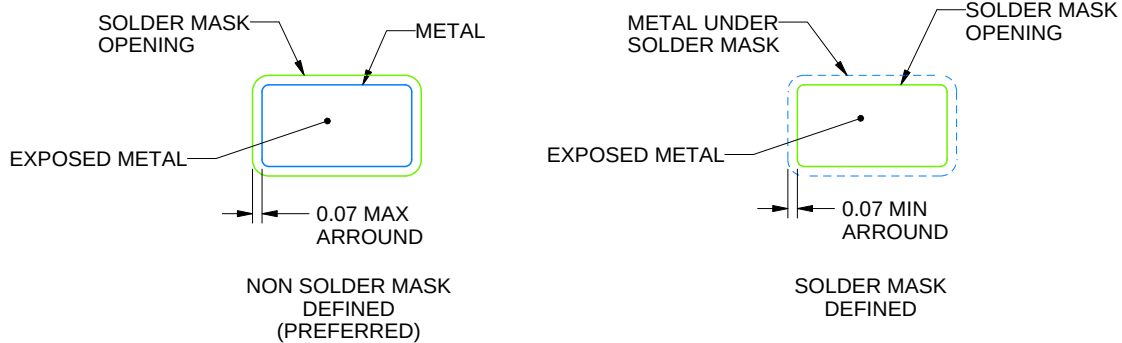
DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:15X



SOLDER MASK DETAILS

4214839/E 09/2019

NOTES: (continued)

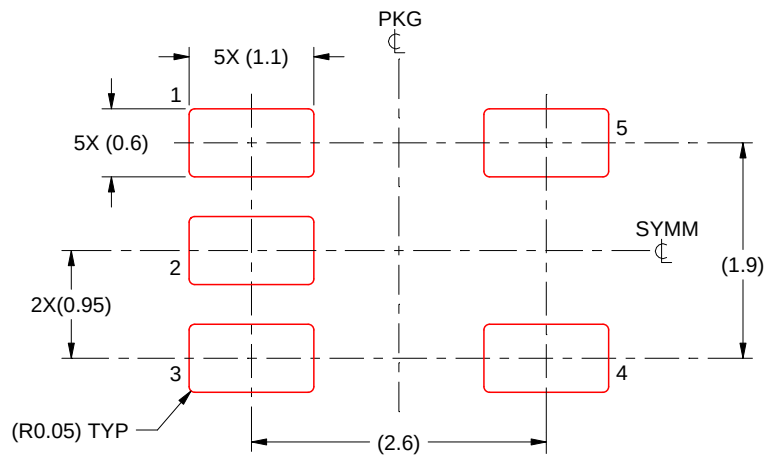
5. Publication IPC-7351 may have alternate designs.
6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:15X

4214839/E 09/2019

NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
8. Board assembly site may have different recommendations for stencil design.

重要声明和免责声明

TI 均以“原样”提供技术性 & 可靠性数据（包括数据表）、设计资源（包括参考设计）、应用或其他设计建议、网络工具、安全信息和其他资源，不保证其中不含任何瑕疵，且不做任何明示或暗示的担保，包括但不限于对适销性、适合某特定用途或不侵犯任何第三方知识产权的暗示担保。

所述资源可供专业开发人员应用 TI 产品进行设计使用。您将对以下行为独自承担全部责任：(1) 针对您的应用选择合适的 TI 产品；(2) 设计、验证并测试您的应用；(3) 确保您的应用满足相应标准以及任何其他安全、安保或其他要求。所述资源如有变更，恕不另行通知。TI 对您使用所述资源的授权仅限于开发资源所涉及 TI 产品的相关应用。除此之外不得复制或展示所述资源，也不提供其它 TI 或任何第三方的知识产权授权许可。如因使用所述资源而产生任何索赔、赔偿、成本、损失及债务等，TI 对此概不负责，并且您须赔偿由此对 TI 及其代表造成的损害。

TI 所提供产品均受 TI 的销售条款 (<http://www.ti.com.cn/zh-cn/legal/termsofsale.html>) 以及 [ti.com.cn](http://www.ti.com.cn) 上或随附 TI 产品提供的其他可适用条款的约束。TI 提供所述资源并不扩展或以其他方式更改 TI 针对 TI 产品所发布的可适用的担保范围或担保免责声明。

邮寄地址：上海市浦东新区世纪大道 1568 号中建大厦 32 楼，邮政编码：200122
Copyright © 2020 德州仪器半导体技术（上海）有限公司